

**Inchange Semiconductor**

**Product Specification**

**Silicon PNP Power Transistors**

**2SA1184**

**DESCRIPTION**

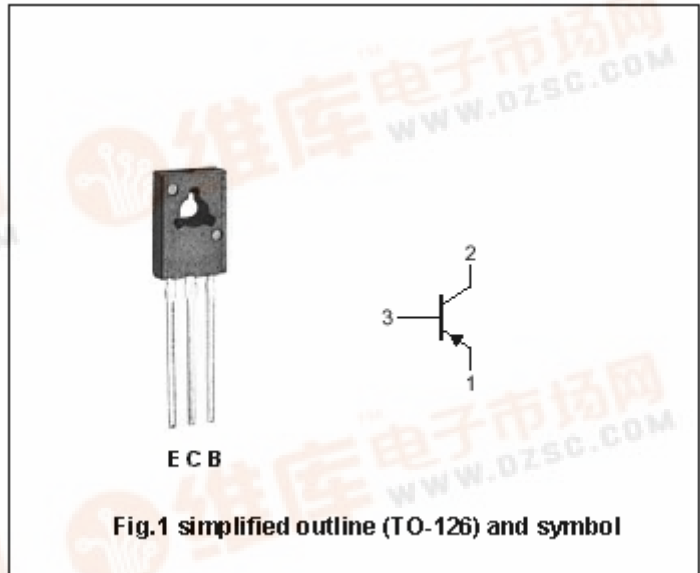
- With TO-126 package
- High breakdown voltage

**APPLICATIONS**

- Audio frequency power amplifier
- High frequency power amplifier

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-120	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-120	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-1	A
I <sub>B</sub>	Base current		-0.1	A
P <sub>D</sub>	Total power dissipation	T <sub>a</sub> =25°C	1.5	W
		T <sub>C</sub> =25°C	15	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~+150	°C

## Silicon PNP Power Transistors

## 2SA1184

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA; I <sub>B</sub> =0	-120			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-10 μ A; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-500mA; I <sub>B</sub> =-50mA			-1.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-500mA ; V <sub>CE</sub> =-5V			-1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-120V; I <sub>E</sub> =0			-1	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-1	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-100mA ; V <sub>CE</sub> =-5V	80		240	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A ; V <sub>CE</sub> =5V		120		MHz

